

In the Abstract:

~~Integrated semiconductor structure~~

~~The invention relates to a~~An integrated semiconductor structure, having has a substrate (1), ~~at least one~~a semiconductor element (2) located on the substrate (1), a pad metal (3) ~~having a surface (F), a multiplicity of~~ metal layers (4.x) ~~which are located between the pad metal (3) and the~~ substrate (1), and ~~a multiplicity of insulation layers (5.y), which that~~ separate the metal layers (4.x) from one another, ~~t.~~The pad metal (3) ~~extendings~~ at least over at least -part of the ~~at least one~~ semiconductor element (2).

~~The invention is distinguished by the fact that,~~b Below the surface (F) of the pad metal (3), at least the top two metal layers (4.x, 4.x-1) ~~have a~~ structure ~~which in each case at least includes two~~ or more adjacent interconnects (4.x.z, 4.x-1.z).